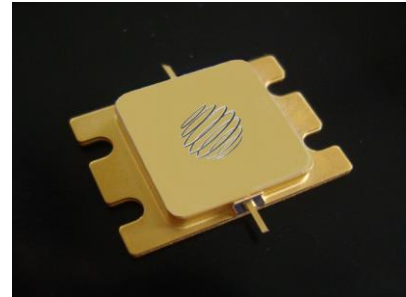


NGN1214H1S-M50 is a Gallium Nitride RF power transistor internally matched to 50Ω. It is developed for high power amplifiers and it is ideal for pulsed radar applications. This transistor has hermetically sealed package to enable use in applications with high reliability requirements.

Features

- 50W output power
- 17 dB power gain
- 50Ω input and output impedance
- 65% power added efficiency

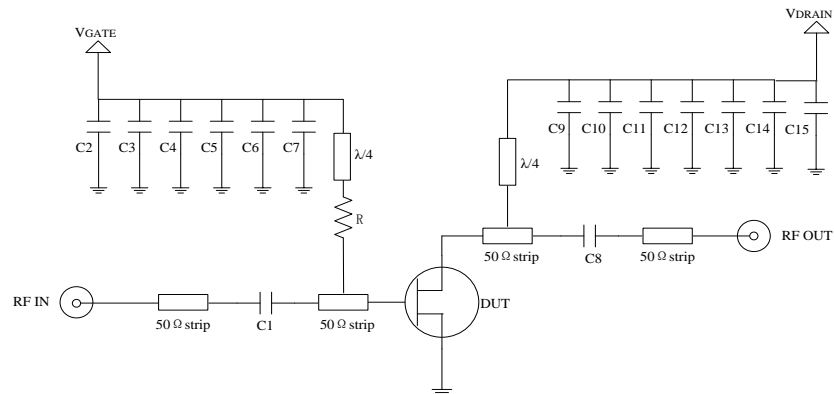


Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$		-3.0		VDC	$V_{DS} = 10\text{ V}, I_D = 5.2\text{ mA}$
Gate Quiescent Voltage	$V_{GS(Q)}$		-2.8		VDC	$V_{DS} = 50\text{ V}, I_D = 50\text{ mA}$
Saturated Drain Current ²	I_{DS}		5.2		A	$V_{DS} = 6.0\text{ V}, V_{GS} = 2.0\text{ V}$
RF Characteristics (VDD= 50V, Tc = 25°C, F = 1.2-1.4 GHz, IDQ = 50mA, Pulse duration = 250μs/10%)						
Gain	G_{LS}		17		dB	$P_{in} = 30\text{ dBm}$
Power	P_{SAT}		50		W	$P_{in} = 30\text{ dBm}$
Input Return Loss	S_{11}		-10		dB	$P_{in} = 10\text{ dBm}$
PAE	η	-	65	-	%	$P_{in} = 30\text{ dBm}$
Output Mismatch	VSWR			5:1	ψ	

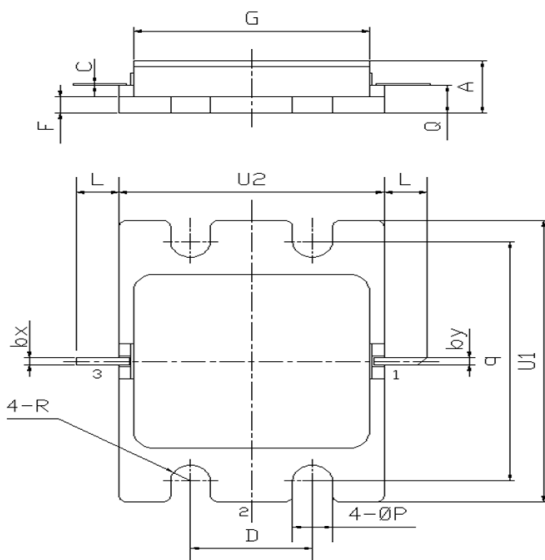
Maximum Ratings	Symbol	Rating	Units	Conditions
Parameter				
Drain-Source Voltage	V_{DSS}	150	V	25°C
Gate-Source Voltage	V_{GS}	-10, +2	V	25°C
Storage temperature	T_{STG}	-65 - 150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Drain Current	$I_{D_{MAX}}$	3.2	A	25°C
Maximum Forward Gate Current	$I_{G_{MAX}}$	5.2	mA	25°C
Duty cycle	DC	10	%	

Subject to change without notice.

Evaluation Circuit



Pos.	Descr.
R	10 Ω
C1,C7,C8,C9	10 pF
C2,C3,C13,C14	1 μF
C4, C12	10 nF
C5, C11	33 pF
C6, C10	1 nF
C15	220 μF
PCB RO5880	$\epsilon_r=3.66$



Item	Measure mm	
	Min	Max
A	4.05	4.5
bx	0.55	0.65
by	0.55	0.65
C	0.05	0.15
D	7.85	8.15
F	1.2	1.6
L	2.85	3.15
G	15.35	15.65
ØP	2.45	2.75
Q	2.25	2.55
q	20.2	20.6
R	1.15	1.45
U1	23.8	24.2
U2	17.2	17.6

Subject to change without notice.